

Docket No. 8733.126.00

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Duck-Kyun CHO

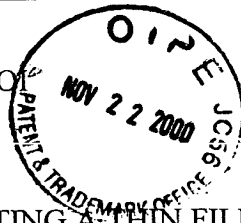
SERIAL NO: 09/170,625

FILING DATE: October 13, 1998

FOR: METHOD FOR FABRICATING A THIN FILM TRANSISTOR

GAU: 2823

EXAMINER: S. Hawranek



*Response  
#14  
12/1/00*

**REQUEST FOR RECONSIDERATION**

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated May 26, 2000, Applicant requests that the application be reconsidered in view of the following comments.

RECEIVED

DEC 04 2000

**REMARKS**

TECHNOLOGY CENTER 2800

The May 26, 2000 Office Action rejected claims 1-36 under 35 U.S.C. §103 as being unpatentable over Maekawa (USP 6,066,547) in combination with Arai et al. (USP 5,576,222) and Seung-Ik Jun (Aepse '97) and/or Cristoloveanu et al. (SOI). With all respect to the Examiner, the rejections of claims 1-36 are traversed.

The subject invention relates to fabricating thin film transistors by using both a thermal treatment and electric fields to crystallize an amorphous silicon layer (reference the pending independent claims 1, 14, and 25). In contrast, Maekawa teaches fabricating thin film transistors using only thermal treatments to crystallize amorphous silicon, while Arai et al. teaches forming an amorphous silicon layer that is then converted into poly-silicon using heat. Recognizing that Maekawa and Arai et al. do not teach fabricating thin film transistors by crystallizing amorphous silicon using heat and electric fields, the Patent Office relies on Seung-Ik Jun (Aepse '97) and/or